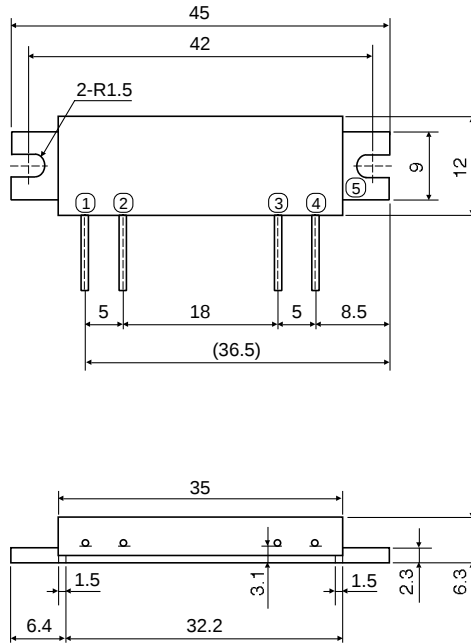


SILICON MOS FET POWER AMPLIFIER, 889-915MHz, 3.8W, FM PORTABLE RADIO

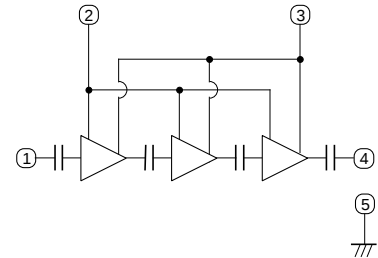
OUTLINE DRAWING

Dimensions in mm



H50

BLOCK DIAGRAM



PIN:

①Pin : RF INPUT

②VGG : GATE BIAS SUPPLY

③VDD : DRAIN BIAS SUPPLY

④PO : RF OUTPUT

⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
VDD	Supply voltage	ZG=ZL=50Ω	9	V
VGG	Gate bias voltage		5.5	V
Pin	Input power	f=889-915MHz, ZG=ZL=50Ω	6	mW
PO	Output power	f=889-915MHz, ZG=ZL=50Ω	6	W
TC (OP)	Operation case temperature	f=889-915MHz, ZG=ZL=50Ω	-30 to +100	°C
Tstg	Storage temperature		-40 to +100	°C

Note. Above parameters are guaranteed independently.

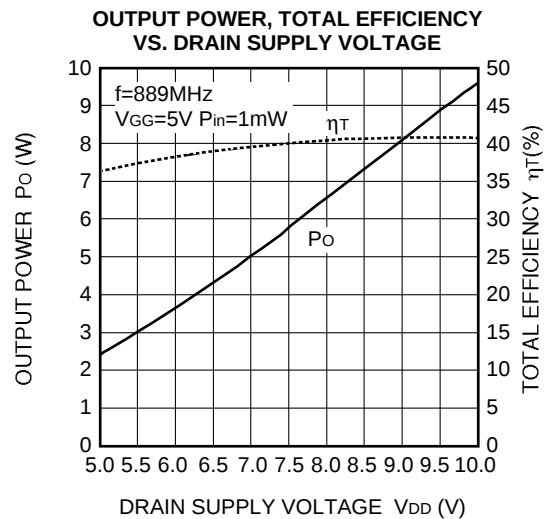
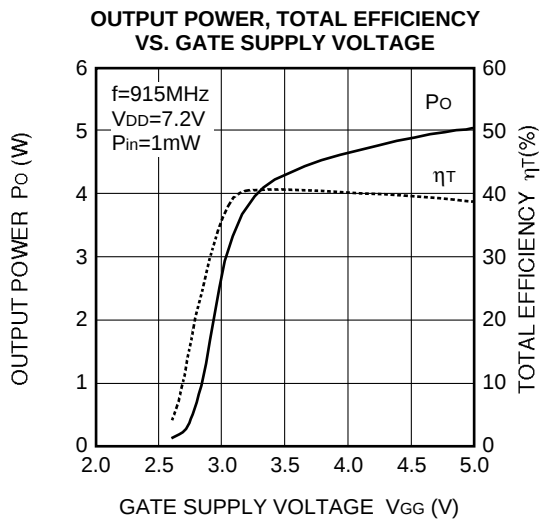
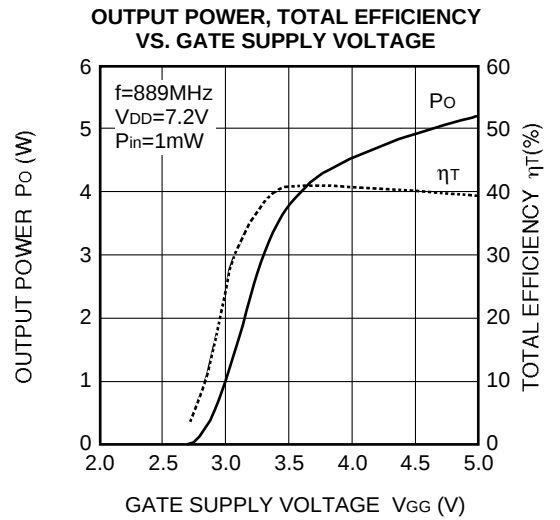
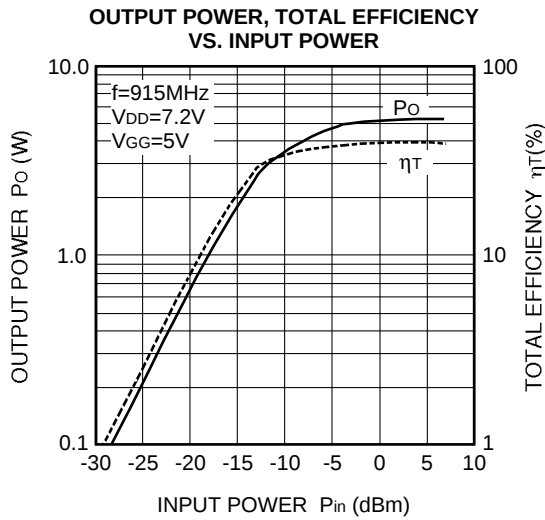
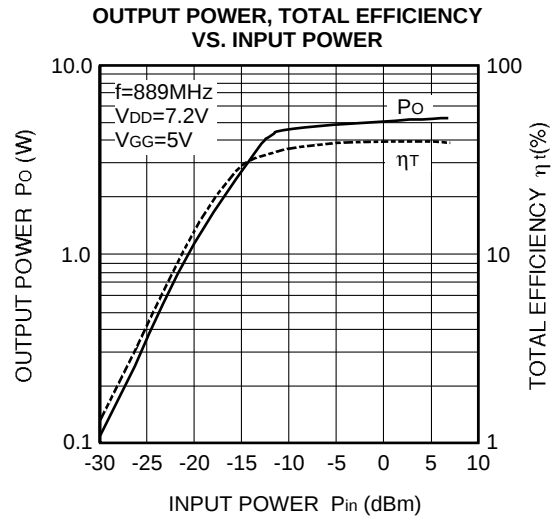
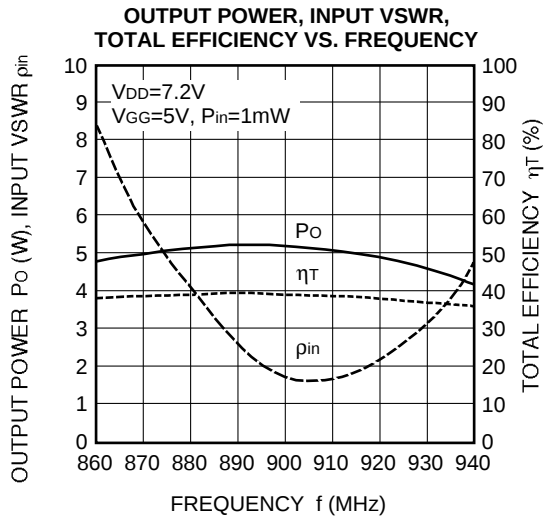
ELECTRICAL CHARACTERISTICS (Tc=25°C, ZG=ZL=50Ω unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		889	915	MHz
PO	Output power	VDD=7.2V, VGG=5V, Pin=1mW, ZG=ZL=50Ω	3.8	-	W
2fo	2nd. harmonic			-30	dBc
pin	Input VSWR			4	-
ηT	Total efficiency	PO=3.8W(VGG=Adjust), VDD=7.2V, Pin=1mW, ZG=ZL=50Ω	30		%
-	Stability	ZG=ZL=50Ω, VDD=5-7.2V, Load VSWR <4:1	No parasitic oscillation		-
-	Load VSWR tolerance	VDD=9V, Pin=1mW, PO=3.8W (VGG Adjust), ZL=20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

SILICON MOS FET POWER AMPLIFIER, 889-915MHz, 3.8W, FM PORTABLE RADIO

TYPICAL PERFORMANCE DATA



SILICON MOS FET POWER AMPLIFIER, 889-915MHz, 3.8W, FM PORTABLE RADIO

